

ABSTRACT OF THE DISCLOSURE

In an MRAM having main and sub-structures, selecting transistors are arranged so as to meet the arrangement order of main wordlines, sub-wordlines and the selecting transistors.

5 The selecting transistor is driven to cause a snap back phenomenon to occur. As a result, data can be written to a memory cell using a substrate current, not a channel current. Moreover, a data may be written into a selected memory cell by discharge the charge which is charged in the main and sub

10 word lines corresponding to the memory cell.